



Green Device Available
 Super Low Gate Charge
 Excellent CdV/dt effect decline
 Advanced high cell density Trench technology

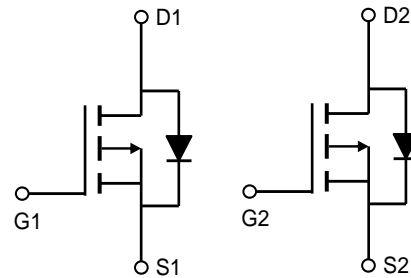
Description

The WLB4807 is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

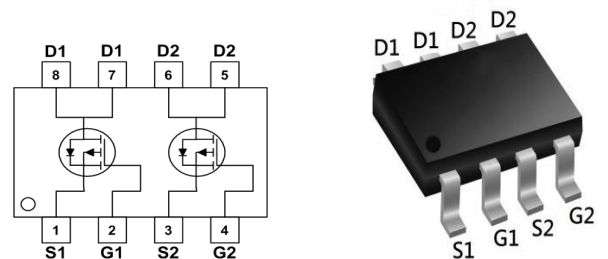
The WLB4807 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

Product Summary

BVDSS	RDSON	ID
-30V	12mΩ	-10.5A



SOP8 Pin Configuration



Absolute Maximum Ratings (TA=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units	
V _{DSS}	Drain-Source Voltage	-30	V	
V _{GSS}	Gate-Source Voltage	±20	V	
I _D	Continuous Drain Current	T _A = 25°C	-10.5	A
		T _A = 100°C	-5.9	A
I _{DM}	Pulsed Drain Current ^{note1}	-36	A	
E _{AS}	Single Pulsed Avalanche Energy ^{note2}	25	mJ	
P _D	Power Dissipation	T _A = 25°C	3.3	W
R _{θJA}	Thermal Resistance, Junction to Ambient	38	°C/W	
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C	



Electrical Characteristics (T_J=25 °C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain- Source Breakdown Voltage	V _{GS} =0V , I _D =-250uA	-30	---	---	V
ΔBV _{DSS} /ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =- 1mA	---	-0.022	---	V/ °C
R _{DS(ON)}	Static Drain- Source On-Resistance ²	V _{GS} =- 10V , I _D =-6A	---	12	15	mΩ
		V _{GS} =-4.5V , I _D =-4A	---	20	35	
V _{GS(th)}	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =-250uA	-1.0	---	-2.5	V
ΔV _{GS(th)}	V _{GS(th)} Temperature Coefficient		---	4.6	---	mV/ °C
I _{DSS}	Drain- Source Leakage Current	V _{DS} =-24V , V _{GS} =0V , T _J =25°C	---	---	-1	uA
		V _{DS} =-24V , V _{GS} =0V , T _J =55°C	---	---	-5	
I _{GSS}	Gate- Source Leakage Current	V _{GS} =± 20V , V _{DS} =0V	---	---	±100	nA
g _{fs}	Forward Transconductance	V _{DS} =-5V , I _D =-6A	---	17	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	13	---	Ω
Q _g	Total Gate Charge (-4.5V)	V _{DS} =- 15V , V _{GS} =-4.5V , I _D =-6A	---	12.6	---	nC
Q _{gs}	Gate- Source Charge		---	4.8	---	
Q _{gd}	Gate- Drain Charge		---	4.8	---	
T _{d(on)}	Turn-On Delay Time	V _{DD} =- 15V , V _{GS} =- 10V , R _G =3.3Ω , I _D =-6A	---	4.6	---	ns
T _r	Rise Time		---	14.8	---	
T _{d(off)}	Turn-Off Delay Time		---	41	---	
T _f	Fall Time		---	19.6	---	
C _{iss}	Input Capacitance	V _{DS} =- 15V , V _{GS} =0V , f=1MHz	---	1345	---	PF
C _{oss}	Output Capacitance		---	194	---	
C _{rss}	Reverse Transfer Capacitance		---	158	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I _S	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	-6.5	A
I _{SM}	Pulsed Source Current ^{2,5}		---	---	-26	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _S =- 1A , T _J =25°C	---	---	-1.2	V
t _{rr}	Reverse Recovery Time	I _F =-6A , dI/dt=100A/μs , T _J =25°C	---	16.3	---	ns
Q _{rr}	Reverse Recovery Charge		---	5.9	---	nC

Note :

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width ≤ 300 us , duty cycle ≤ 2%
3. The EAS data shows Max. rating . The test condition is V_{DD}=-25V, V_{GS}=- 10V, L=0. 1mH, I_{AS}=-38A
4. The power dissipation is limited by 150°C junction temperature
5. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.



Typical Performance Characteristics

Figure 1 : Output Characteristics

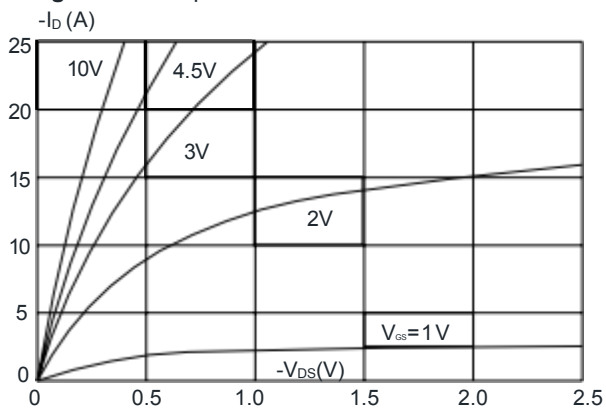


Figure 2 : Typical Transfer Characteristics

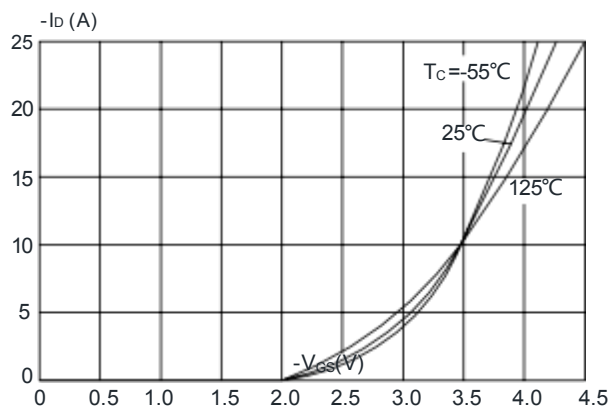


Figure 3 : On-resistance vs. Drain Current

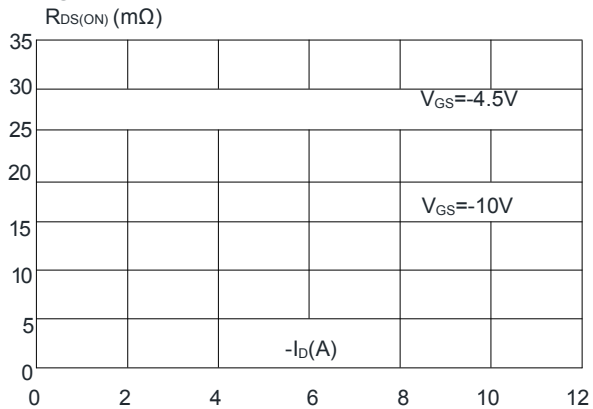


Figure 4 : Body Diode Characteristics

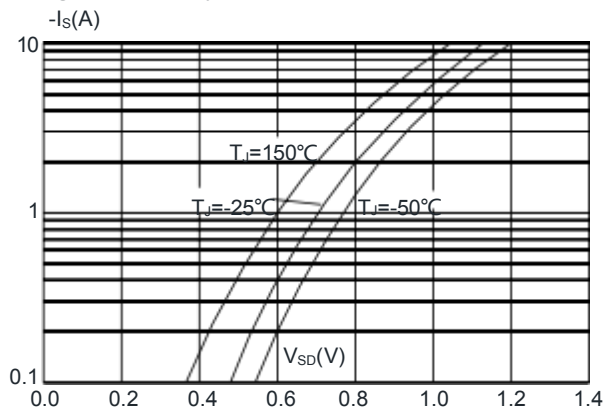


Figure 5 : Gate Charge Characteristics

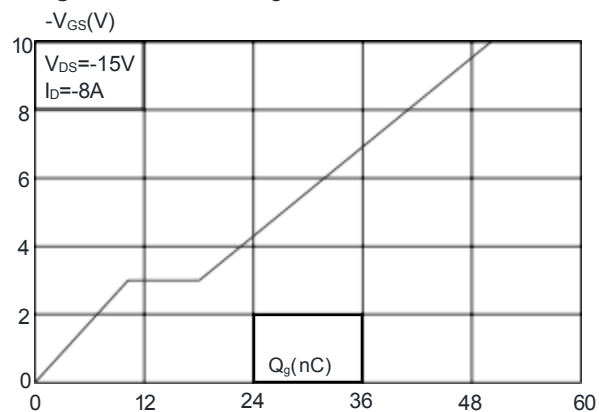
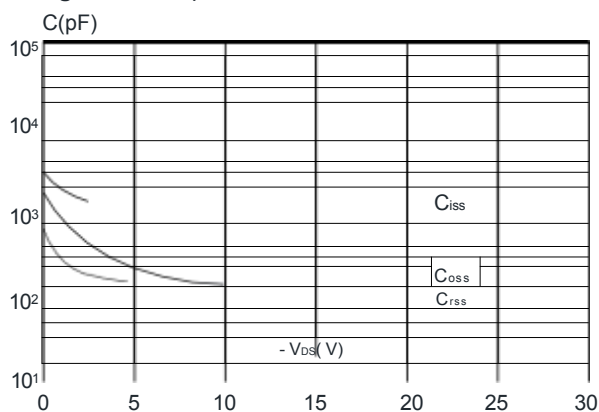


Figure 6 : Capacitance Characteristics





Dual P-Ch 30V Fast Switching MOSFETs

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

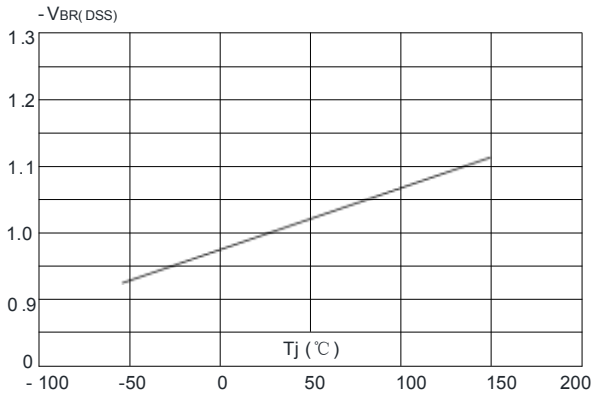


Figure 8: Normalized on Resistance vs. Junction Temperature

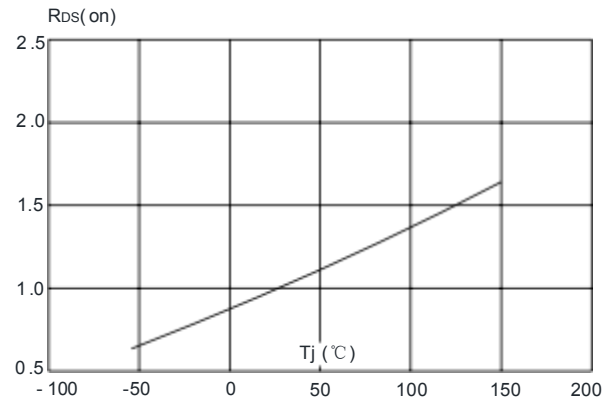


Figure 9: Maximum Safe Operating Area

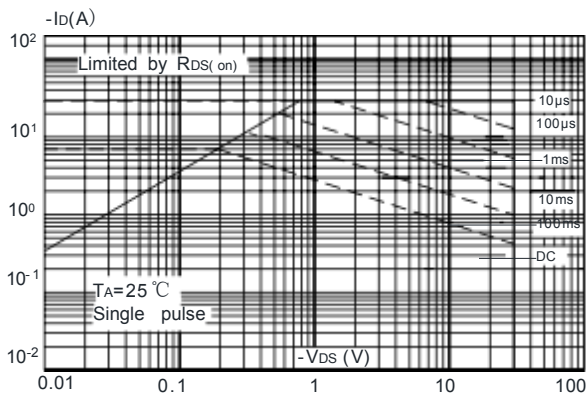
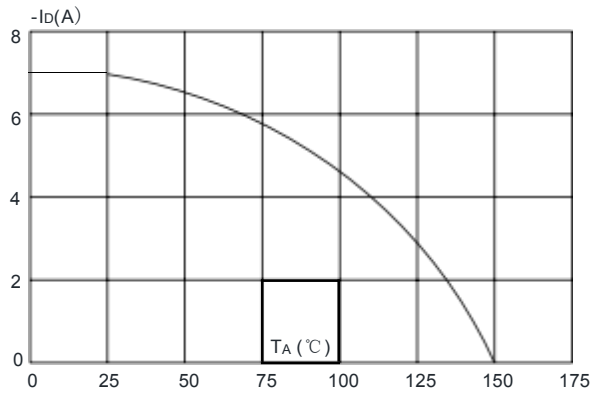
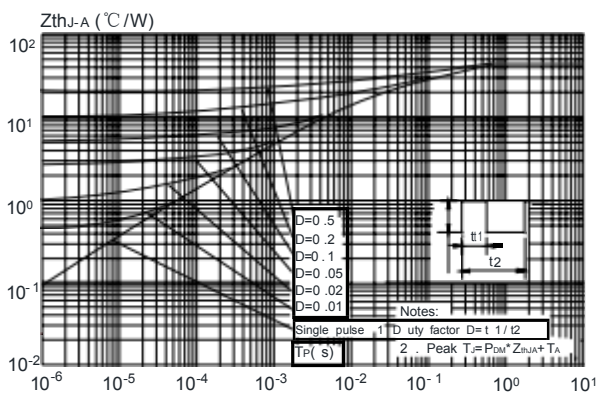


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

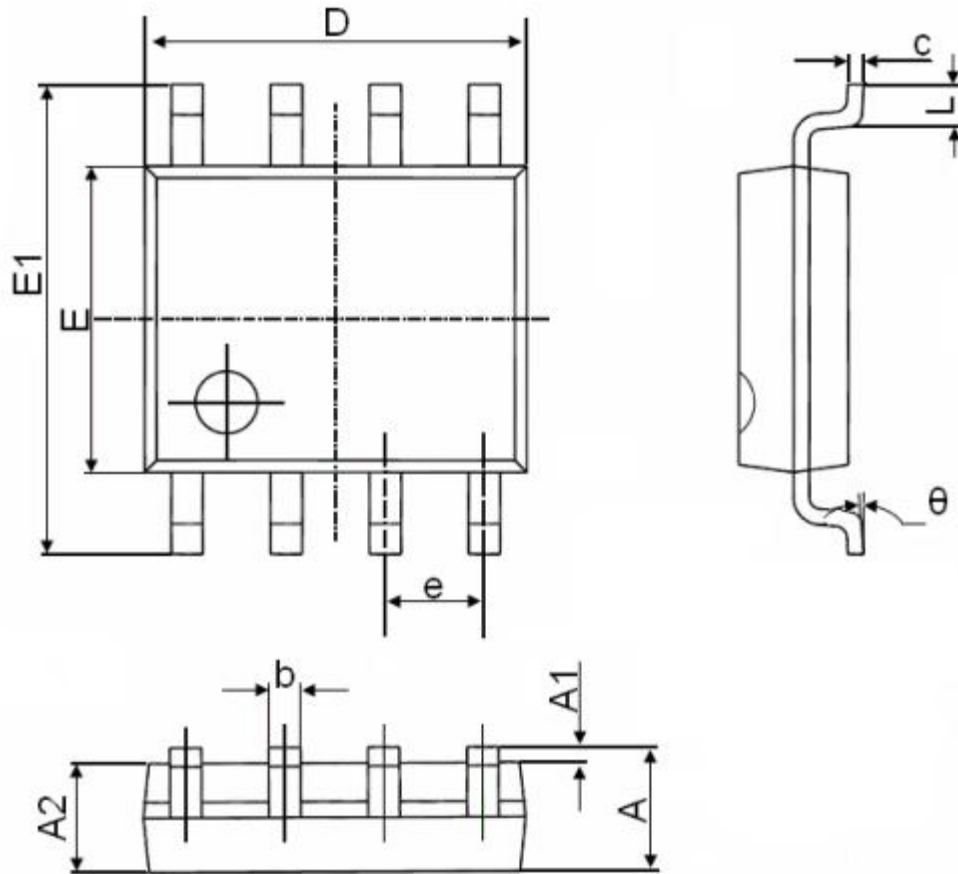


Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





Package Mechanical Data- SOP-8



COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	1.40	1.60	1.80
A1	0.05	0.15	0.25
A2	1.35	1.45	1.55
b	0.30	0.40	0.50
c	0.153	0.203	0.253
D	4.80	4.90	5.00
E	3.80	3.90	4.00
E1	5.80	6.00	6.20
L	0.45	0.70	1.00
θ	2°	4°	6°
L1	1.04 REF		
e	1.27 BSC		
R1	0.07 TYP		
R2	0.07 TYP		



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